

ABSTRACT OF THE DISCLOSURE

A field plate portion (5) overhanging a drain side in a visored shape is formed in a gate electrode (2). A multilayered film including a SiN film (21) and a SiO₂ film (22) is formed beneath the field plate portion (5). The SiN film (21) is formed so that a surface of an AlGaN electron supply layer (13) is covered therewith.